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Examiner: M. Marcheschi
Art Unit: 1755

Claims

1 – 14 (Cancelled)

15. (New) A process for chemical mechanical polishing of a surface, said process comprising:

- a. subjecting said surface to mechanical abrasion; and
- b. delivering a chemical polishing slurry to said surface;

wherein the step of subjecting said surface to mechanical abrasion is intermittently stopped but the delivery of a chemical polishing slurry to said surface is continuous.

16. (New) A process according to claim 15 wherein the mechanical abrasion comprises rotating a polishing pad in contact with said surface.

17. (New) A process according to claim 15 wherein the surface comprises a semiconducting layer.

18. (New) A process according to claim 15 wherein the delivering of the chemical polishing slurry comprises a puddle on said surface.

19. (New) A process for chemical mechanical polishing of a surface, said process comprising:

- a. contacting said surface with a polishing pad which polishing pad is placed in motion relative to said surface while in contact with said surface;
- b. delivering a chemical polishing slurry to said surface;

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wherein for periods of time during said process the composition of the chemical polishing slurry being delivered to said surface is changed such that it comprises no abrasive particles during said periods of time.

20. (New) A process according to claim 19 wherein the surface comprises a semiconducting layer.

21. (New) A process according to claim 19 wherein the delivery of the chemical polishing slurry comprises a puddle on said surface.